

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	738	silicon near10 substrate near10 (dielectric or oxide) near10 (silicon adj carbide)	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/04 14:33
L2	0	1 and FinFET	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/04 14:33
L3	53	1 and silicon adj germanium	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/04 14:35
L4	27	3 and silicon adj oxide	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/04 14:35